

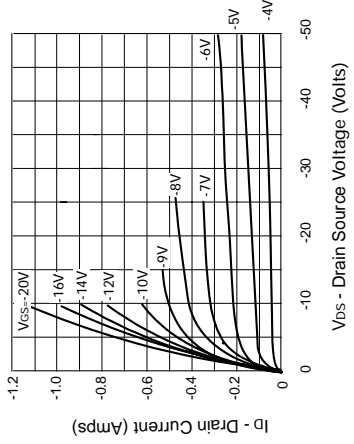


# THE DATASHEET OF ZVP3306A

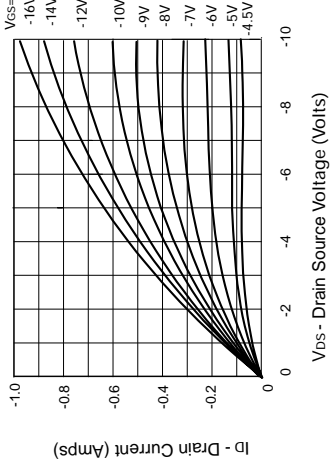


# ZVP3306A

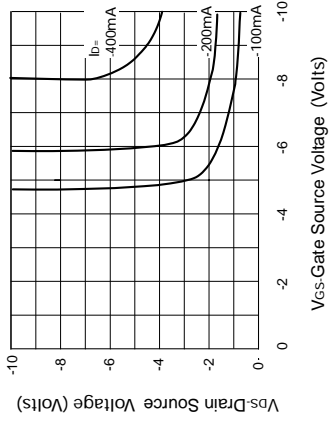
## TYPICAL CHARACTERISTICS



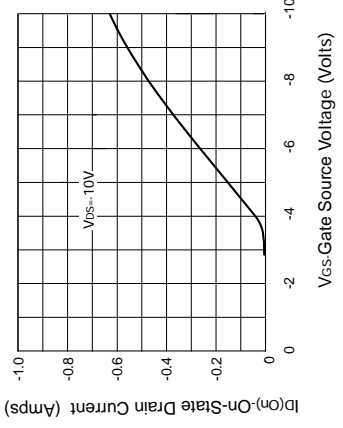
**Output Characteristics**



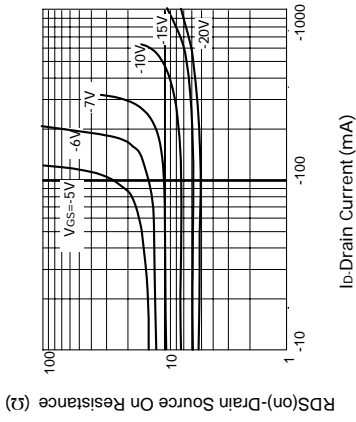
**Saturation Characteristics**



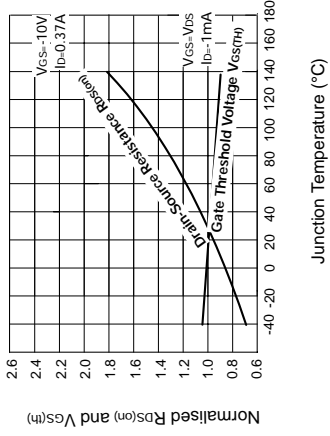
**Voltage Saturation Characteristics**



**Transfer Characteristics**



**On-resistance vs Drain Current**



**Normalised RDS(on) and Vgs(th) vs Temperature**

3-430

# P-CHANNEL ENHANCEMENT MODE VERTICAL DMOS FET

ISSUE 2 – MARCH 94

## FEATURES

- \* 60 Volt V<sub>DS</sub>
- \* R<sub>DS(on)</sub> = 14Ω

## ABSOLUTE MAXIMUM RATINGS

PARAMETER	Limit
Drain-Source Voltage	
Continuous Drain Current at T <sub>amb</sub> =25°C	
Pulsed Drain Current	
Gate Source Voltage	
Power Dissipation at T <sub>amb</sub> =25°C	
Operating and Storage Temperature Range	

## ELECTRICAL CHARACTERISTICS

PARAMETER	SYMBOL
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>
Gate-Source Threshold Voltage	V <sub>GS(th)</sub>
Gate-Body Leakage	I <sub>GSS</sub>
Zero Gate Voltage Drain Current	I <sub>DSS</sub>
On-State Drain Current(1)	I <sub>D(on)</sub>
Static Drain-Source On-State Resistance (1)	R <sub>DS(on)</sub>
Forward Transconductance (1)(2)	g <sub>fs</sub>
Input Capacitance (2)	C <sub>iss</sub>
Common Source Output Capacitance (2)	C <sub>oss</sub>
Reverse Transfer Capacitance (2)	C <sub>rss</sub>
Turn-On Delay Time (2)(3)	t <sub>d(on)</sub>
Rise Time (2)(3)	t <sub>r</sub>
Turn-Off Delay Time (2)(3)	t <sub>d(off)</sub>
Fall Time (2)(3)	t <sub>f</sub>

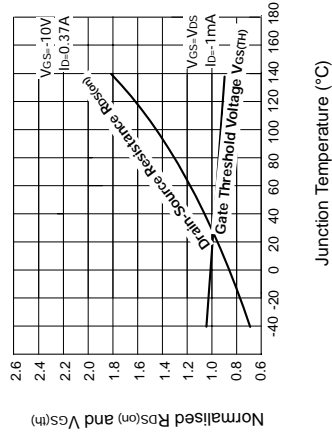
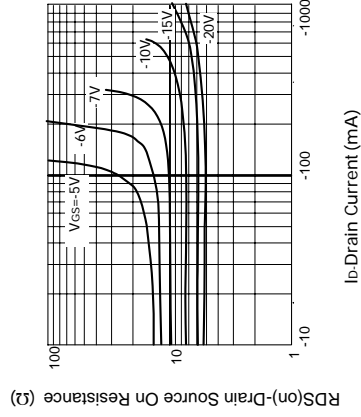
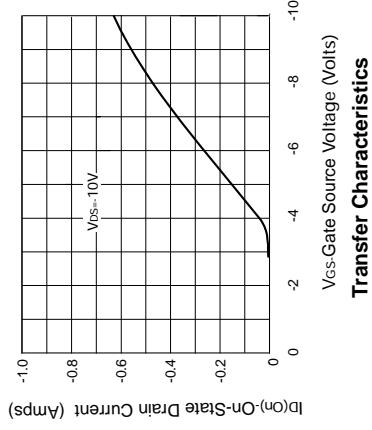
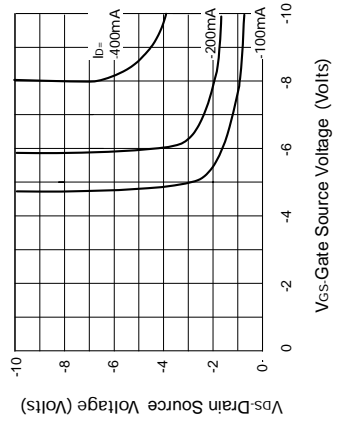
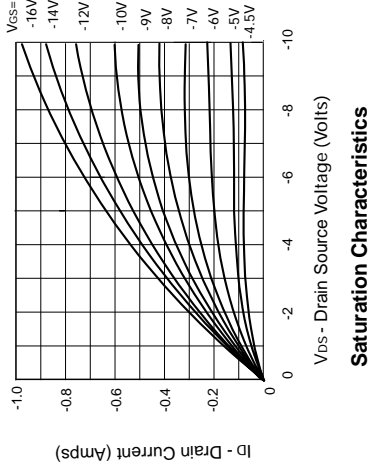
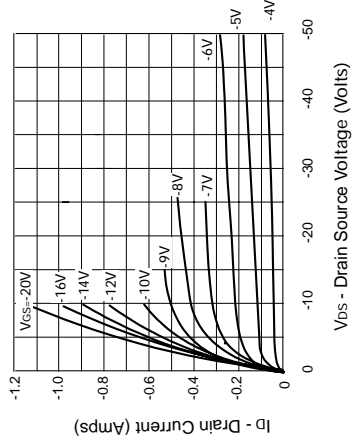
(1) Measured under pulsed conditions. Wire leads included.  
 (2) Sample test.

3-430

Switching times measured with 50Ω source and 50Ω load.

# ZVP3306A

## TYPICAL CHARACTERISTICS



On-resistance vs Drain Current

Normalised RDS(on) and VGS(th) vs Temperature

3-430

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## ELECTRICAL CHARACTERISTICS

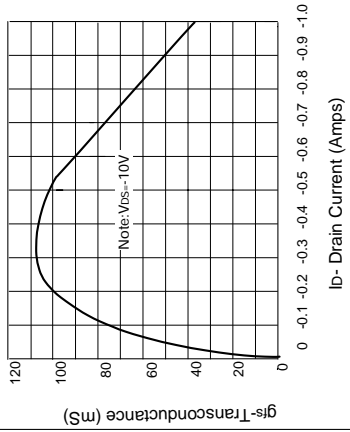
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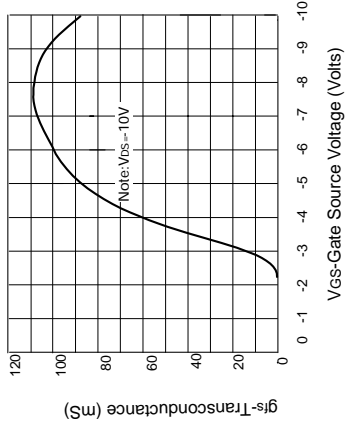
Switching times measured with 50Ω source and 50Ω load.

# ZVP3306A

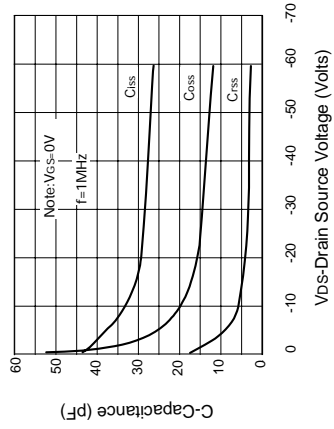
## TYPICAL CHARACTERISTICS



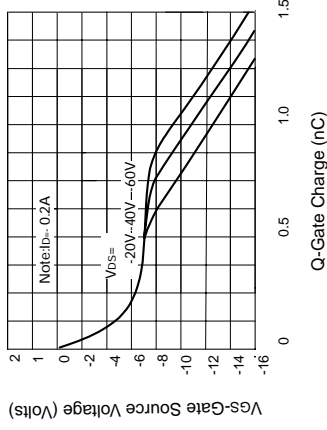
**Transconductance v drain current**



**Transconductance v gate-source voltage**





**Capacitance v drain-source voltage**



**Gate charge v gate-source voltage**

## Looking for pricing, stock, or lifecycle information?

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